



PMBT2907A

60V, 600 mA, PNP switching transistor

6 March 2015

Product data sheet

1. General description

PNP switching transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PMBT2222A

40V variant: PMBT2907

2. Features and benefits

- Single general-purpose switching transistor
- AEC-Q101 qualified

3. Applications

- Switching and linear amplification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CE0}	collector-emitter voltage	open base	-	-	-60	V
I_C	collector current		-	-	-600	mA
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}$; $I_C = -150\text{ mA}$; $T_{amb} = 25\text{ °C}$	100	-	300	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	<p>TO-236AB (SOT23)</p>	<p>sym132</p>
2	E	emitter		
3	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBT2907A	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMBT2907A	%2F

[1] % = placeholder for manufacturing site code

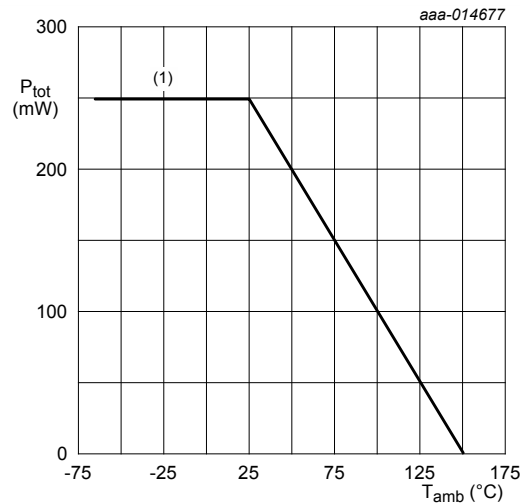
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-60	V
V_{CEO}	collector-emitter voltage	open base	-	-60	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I_C	collector current		-	-600	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-800	mA
I_{BM}	peak base current		-	-200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	250	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	150	°C
T_{stg}	storage temperature		-65	150	°C

[1] Transistor mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



(1) FR4 PCB; standard footprint

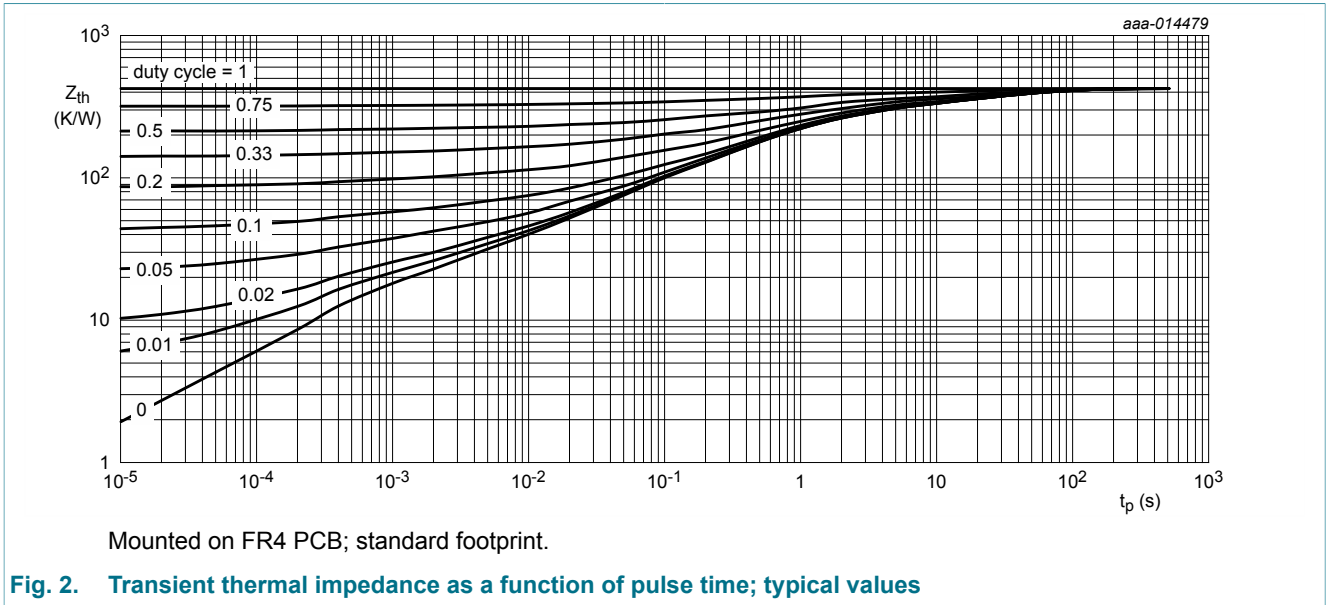
Fig. 1. Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	500	K/W

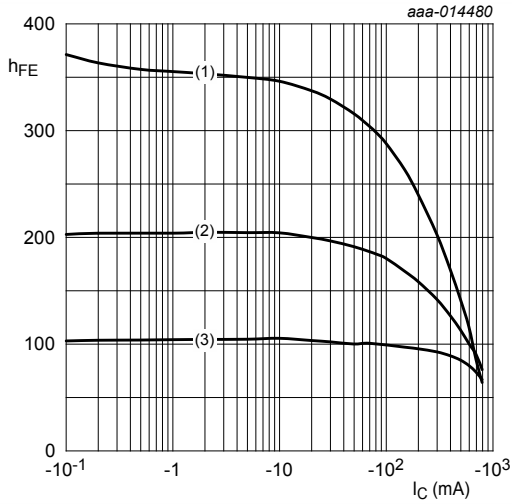
[1] Transistor mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.



10. Characteristics

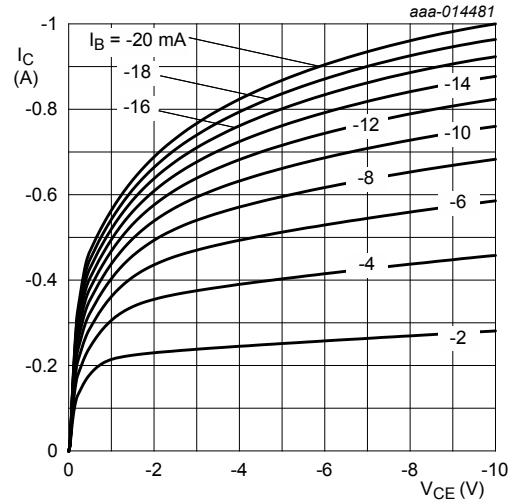
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-10	nA
		V _{CB} = -50 V; I _E = 0 A; T _j = 125 °C	-	-	-10	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-50	nA
h _{FE}	DC current gain	V _{CE} = -10 V; I _C = -0.1 mA; T _{amb} = 25 °C	75	-	-	
		V _{CE} = -10 V; I _C = -1 mA; T _{amb} = 25 °C	100	-	-	
		V _{CE} = -10 V; I _C = -10 mA; T _{amb} = 25 °C	100	-	-	
		V _{CE} = -10 V; I _C = -150 mA; T _{amb} = 25 °C	100	-	300	
		V _{CE} = -10 V; I _C = -500 mA; T _{amb} = 25 °C	50	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -150 mA; I _B = -15 mA; T _{amb} = 25 °C	-	-	-400	mV
		I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C	-	-	-1.6	V
V _{BEsat}	base-emitter saturation voltage	I _C = -150 mA; I _B = -15 mA; T _{amb} = 25 °C	-	-	-1.3	V
		I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C	-	-	-2.6	V
t _d	delay time	I _C = -150 mA; I _{Bon} = -15 mA; I _{Boff} = 15 mA; T _{amb} = 25 °C	-	-	12	ns
t _r	rise time		-	-	30	ns
t _{on}	turn-on time		-	-	40	ns
t _s	storage time		-	-	300	ns
t _f	fall time		-	-	65	ns
t _{off}	turn-off time		-	-	365	ns
C _C	collector capacitance		V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	8
C _E	emitter capacitance	V _{EB} = -2 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	30	pF
f _T	transition frequency	V _{CE} = -20 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	200	-	-	MHz



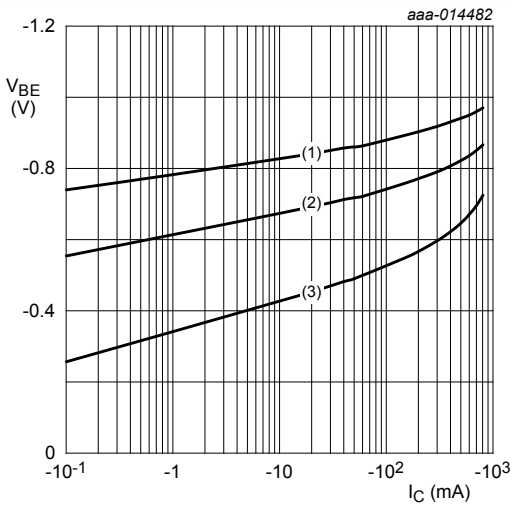
$V_{CE} = -10$ V
 (1) $T_{amb} = 150$ °C
 (2) $T_{amb} = 25$ °C
 (3) $T_{amb} = -55$ °C

Fig. 3. DC current gain as a function of collector current; typical values



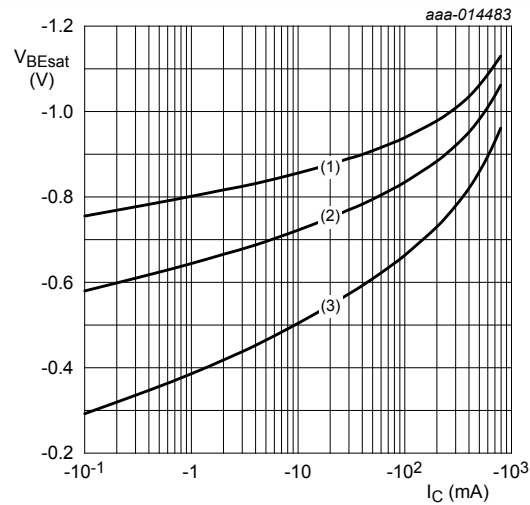
$T_{amb} = 25$ °C

Fig. 4. Collector current as a function of collector-emitter voltage; typical values



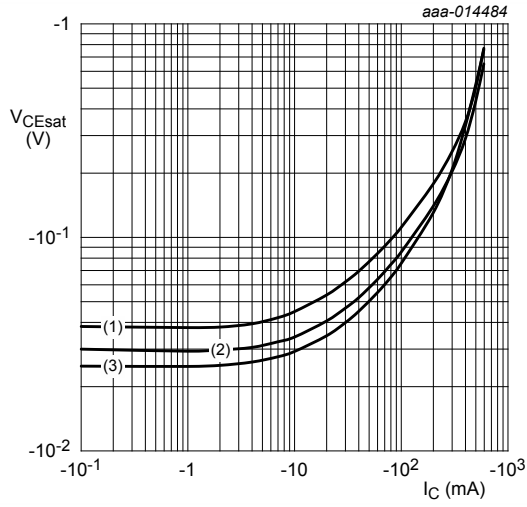
$V_{CE} = -10$ V
 (1) $T_{amb} = -55$ °C
 (2) $T_{amb} = 25$ °C
 (3) $T_{amb} = 150$ °C

Fig. 5. Base-emitter voltage as a function of collector current; typical values



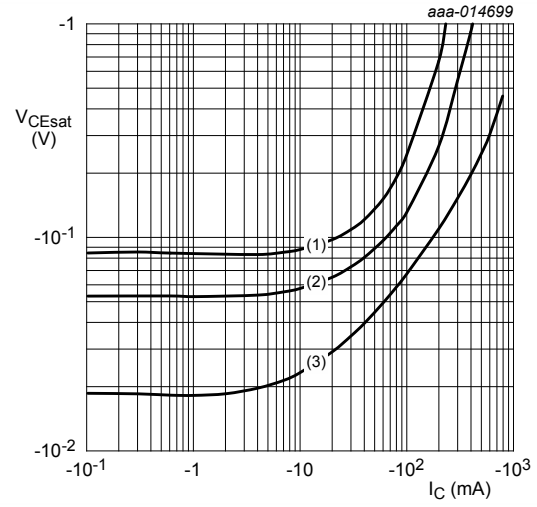
$I_C/I_B = 10$
 (1) $T_{amb} = -55$ °C
 (2) $T_{amb} = 25$ °C
 (3) $T_{amb} = 150$ °C

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

11. Test information

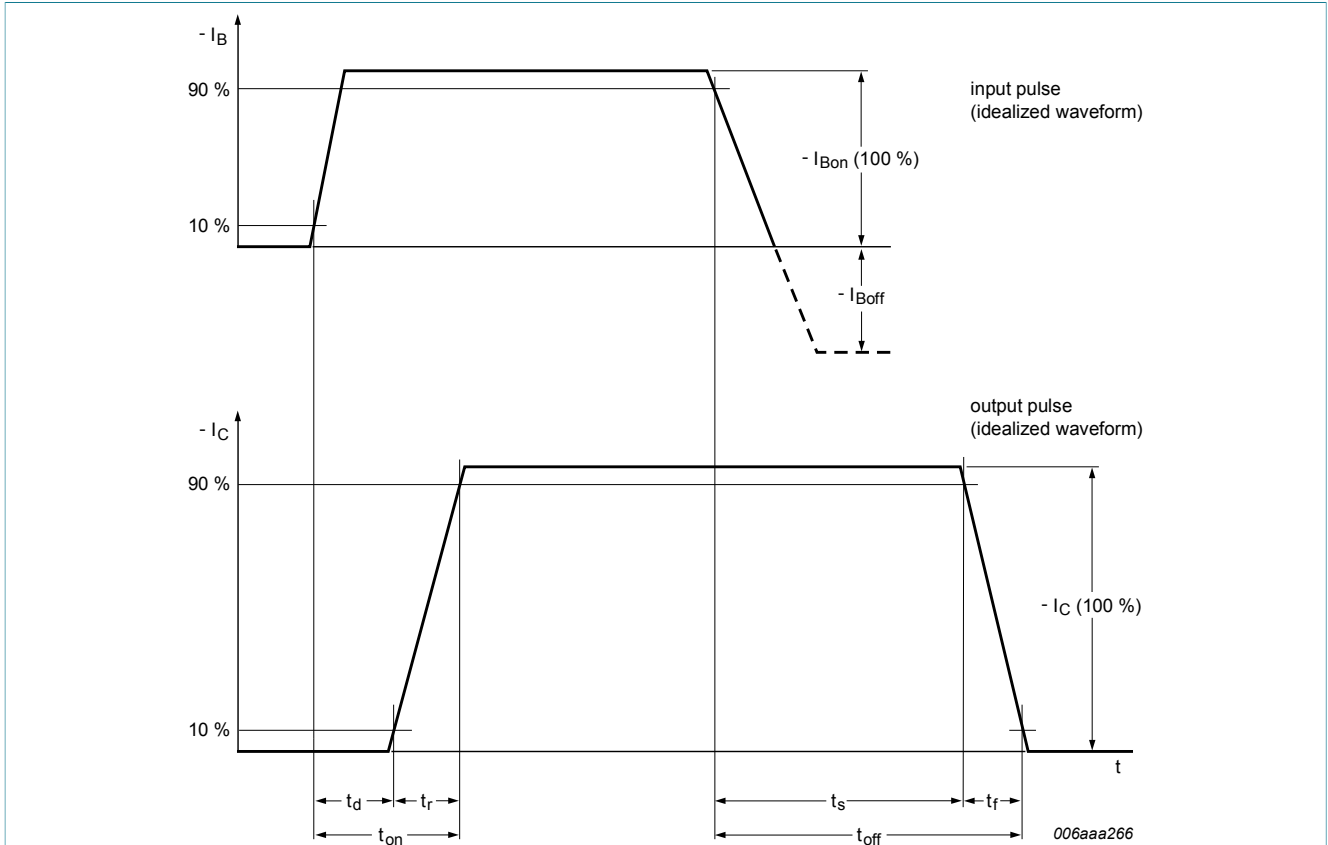


Fig. 9. BISS transistor switching time definition

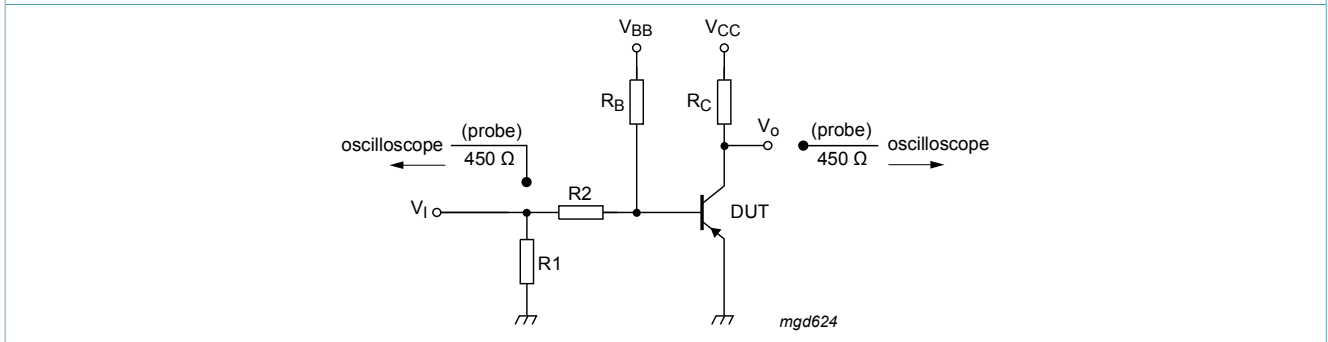


Fig. 10. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

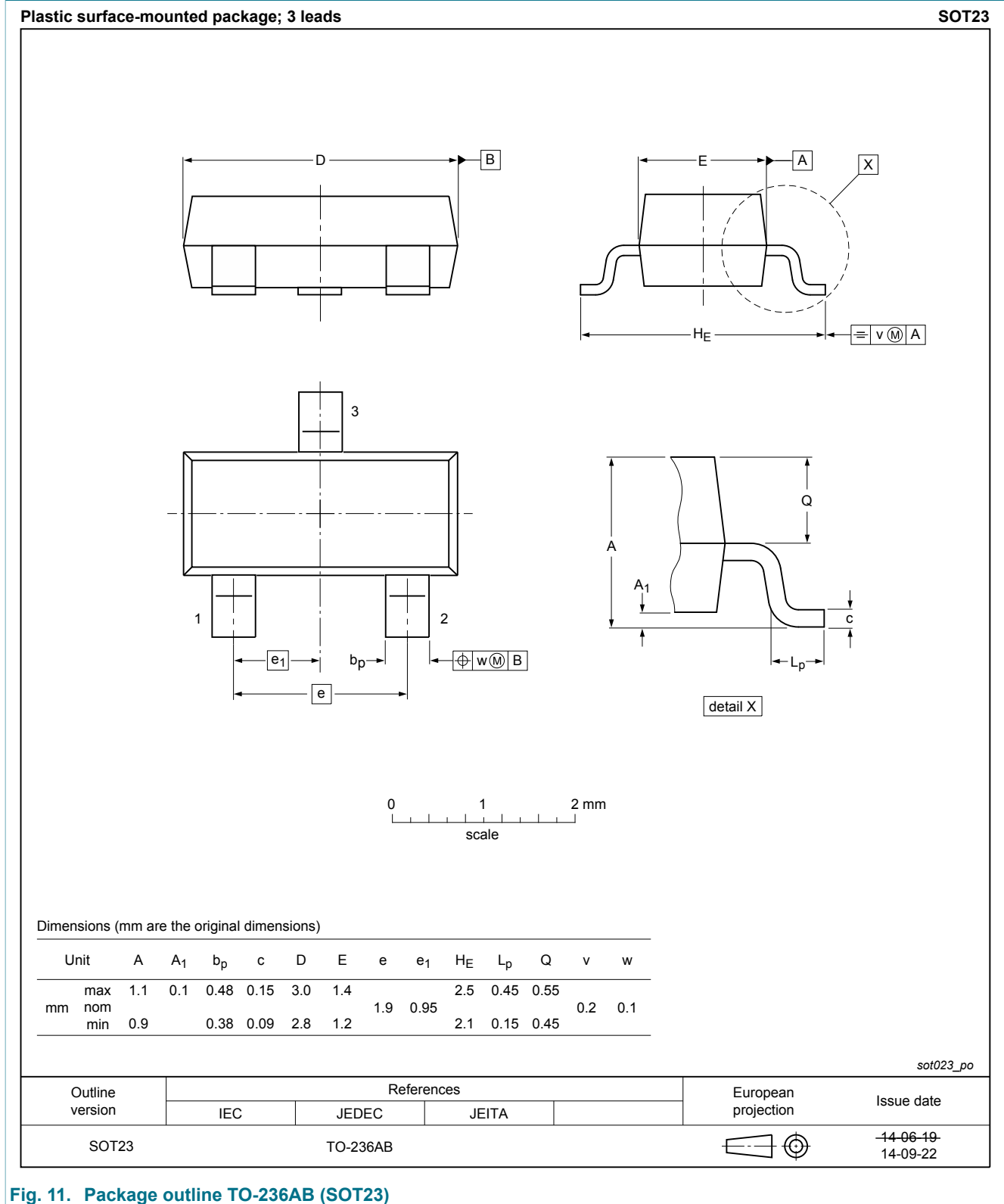


Fig. 11. Package outline TO-236AB (SOT23)

13. Soldering

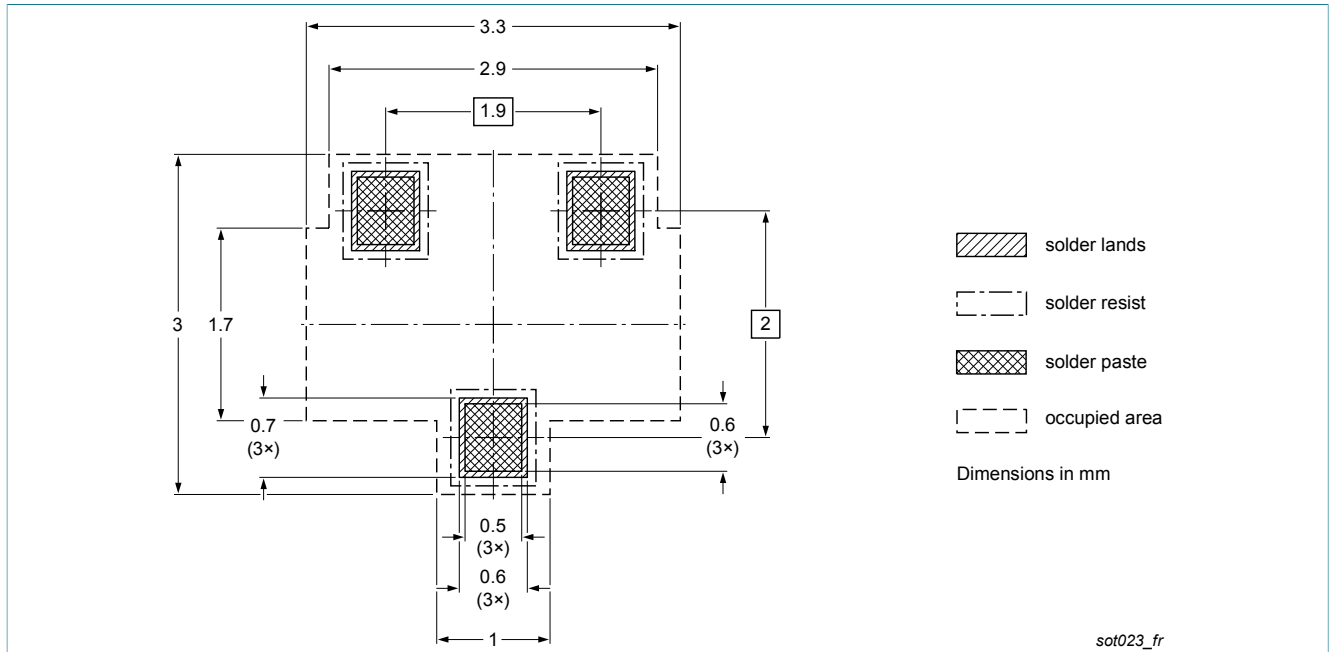


Fig. 12. Reflow soldering footprint for TO-236AB (SOT23)

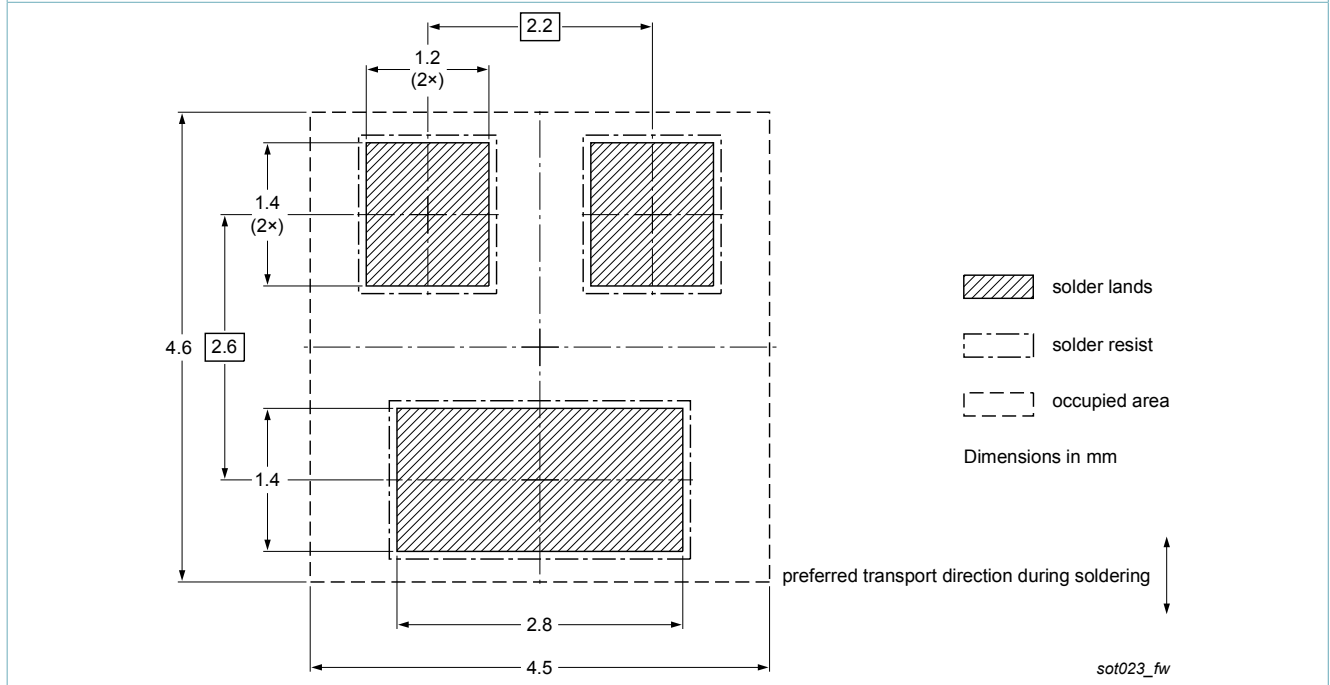


Fig. 13. Wave soldering footprint for TO-236AB (SOT23)